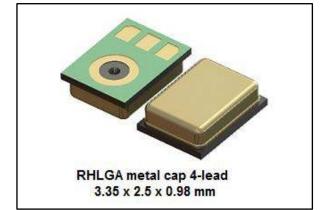
MP23AB01DH



High-performance MEMS audio sensor: fully differential analog bottom-port microphone

Datasheet - production data



Features

- Single supply voltage operation
- Fully differential output
- Omnidirectional sensitivity
- High signal-to-noise ratio
- High bandwidth
- Package compliant with reflow soldering
- High RF immunity
- ECOPACK[®], RoHS, and "Green" compliant

Description

The MP23AB01DH is a compact, low-power microphone built with a capacitive sensing element and an IC interface.

The sensing element, capable of detecting acoustic waves, is manufactured using a specialized silicon micromachining process to produce audio sensors.

The MP23AB01DH has sensitivity of 38 dB \pm 1 dB, an acoustic overload point of 135 dBSPL with minimum 65 dB signal-to-noise ratio.

The MP23AB01DH has fully differential output in order to minimize common mode noise.

The MP23AB01DH is available in a package compliant with reflow soldering and is guaranteed to operate over an extended temperature range from -40 °C to +85 °C.

Table 1: Device summary

Order code	Temp. range (°C) Package		Packing
MP23AB01DH	-40 to +85	(3.35 x 2.5 x 0.98) mm	Tray
MP23AB01DHTR	-40 to +85	(3.35 x 2.5 x 0.98) mm	Tape and reel

This is information on a product in full production.

Contents

Co	ntents		
1	Pin des	cription	3
2	Acousti	ic and electrical specifications	4
	2.1	Acoustic and electrical characteristics	4
	2.2	Frequency response	5
3	Absolut	te maximum ratings	6
4	Applica	tion recommendations	7
	4.1	MP23AB01DH schematic hints	7
5	Packag	e information	8
	5.1	Soldering information	8
	5.2	RHLGA 4-lead package information	9
6	Reliabil	lity tests	
7	Revisio	n history	



1 Pin description

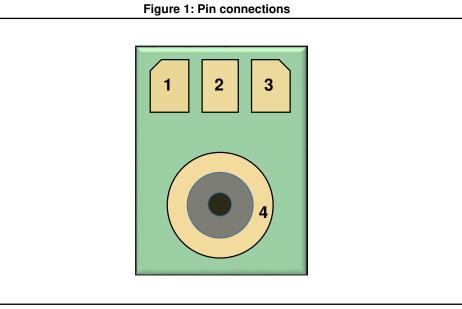


Table 2: Pin description

Pin number	Pin name	Function	
1	Vdd	Power supply	
2	Output–	Output- Negative output signal	
3	Output+ Positive output signal		
4	Ground	Ground	



Acoustic and electrical specifications 2

2.1 Acoustic and electrical characteristics

The values listed in the table below are specified for Vdd = 2.7 V, No Load, Tamb = 25 °C unless otherwise specified.

			11			
Symbol	Parameter	Test condition	Min.	Тур. ⁽¹⁾	Max.	Unit
Vdd	Supply voltage		2.3	2.7	3.6	V
ldd	Current consumption				250	μA
So	Sensitivity	@1 kHz (0 dB = 1 V/Pa)	-39	-38	-37	dBV
SNR	Signal-to-noise ratio	A-weighted (20 Hz - 20 kHz)	65			dB(A)
PSR	Power supply rejection	100 mVpp sine wave @217 Hz		-100		dB
AOP	Acoustic overload point			135		dBSPL
Zout	Output impedance				400	Ω
Cload	Load capacitance				150	pF
Rload	Load resistance		30			κΩ
Тор	Operating temperature range		-40		+85	°C

Table 3: Acoustic and electrical characteristics

Notes:

⁽¹⁾Typical specifications are not guaranteed.

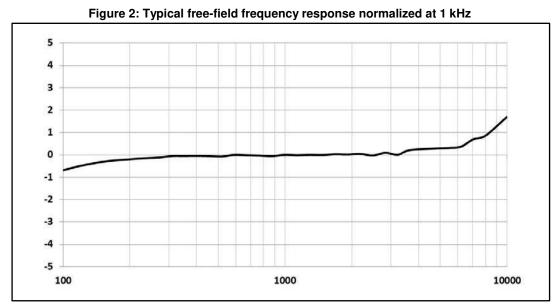
Table 4: Typical distortion specifications at 1 kHz sine wave input				
Parameter	Test condition	Typ. value		
	94 dBSPL	< 0.2%		
	110 dBSPL	< 0.5%		
THD+N	120 dBSPL	< 3%		

130 dBSPL

Table 4. T

< 5%

2.2 Frequency response





3 Absolute maximum ratings

Stresses above those listed as "Absolute maximum ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device under these conditions is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

Symbol	Ratings	Maximum value	Unit
Vdd	Supply voltage	-0.5 to 4.8	V
T _{STG}	Storage temperature range	-40 to +105	°C
ESD	(HBM) ANSI/ESDA/JEDEC JS001	±2000	V
ESD	(MM) EIA/JESD22-A115 ±200		V
ESD	(CDM) JESD22-C101	±750	V
ESD ⁽¹⁾	Per IEC61000-4-2, 3 discharges, 150 pF, 330 Ω direct contact to housing. MIC must be at zero potential before each discharge.	±8000	V

Table 5:	Absolute	maximum	ratings
14010 01	/ 10001010	maximani	raingo

Notes:

⁽¹⁾Bypass capacitor 200 nF or 1 µF (better), is definitely recommended for ESD main clamp integrity.



This device is sensitive to mechanical shock, improper handling can cause permanent damage to the part.



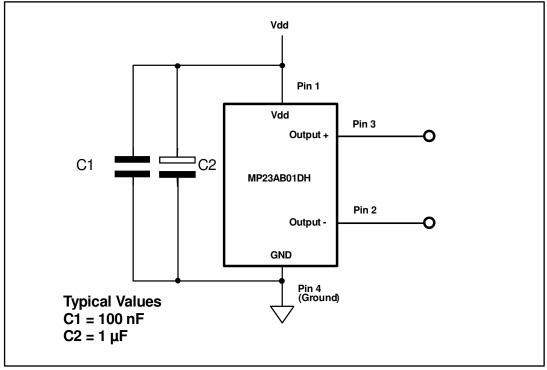
This device is sensitive to electrostatic discharge (ESD), improper handling can cause permanent damage to the part.



4 Application recommendations

4.1 MP23AB01DH schematic hints

Figure 3: MP23AB01DH electrical connections and external component values





5 **Package information**

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

5.1 Soldering information

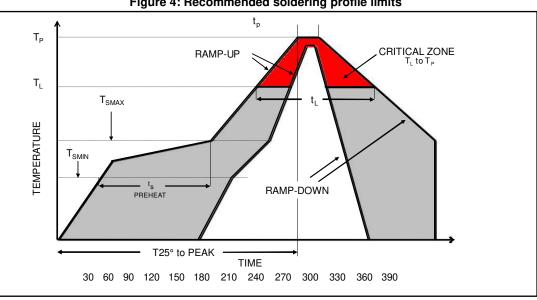


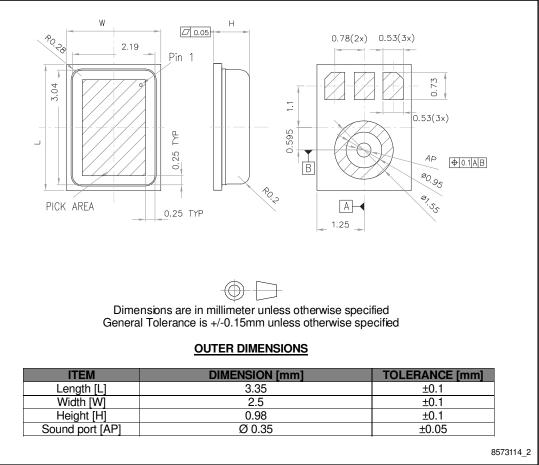


Table 6: Recommended soldering profile limits				
Description	Parameter	Pb free		
Average ramp rate	T∟ to T _P	3 °C/sec max		
Preheat Minimum temperature Maximum temperature Time (T _{SMIN} to T _{SMAX})	T _{SMIN} T _{SMAX} ts	150 °C 200 °C 60 sec to 120 sec		
Ramp-up rate	T_{SMAX} to T_{L}			
Time maintained above liquidus temperature Liquidus temperature	t∟ T∟	60 sec to 150 sec 217 °C		
Peak temperature	TP	260 °C max		
Time within 5 °C of actual peak temperature		20 sec to 40 sec		
Ramp-down rate		6 °C/sec max		
Time 25 °C (t = 25 °C) to peak temperature		8 minutes max		



5.2 RHLGA 4-lead package information







6 Reliability tests

The device passed all reliability tests on three different assembly lots under the following conditions given in the table below.

Test name	Description	Conditions
HTOL: High Temperature Operating Life	The device is stressed in dynamic configuration, approaching the operative max. absolute ratings in terms of junction temperature, load current, internal power dissipation.	Vdd(max) = 3.6 V; Tamb = 125 °C JESD22a108
HTS: High Temperature Storage	The device is stored in an unbiased condition at the maximum temperature allowed by the package materials, sometimes higher than the maximum operative temperature.	Ta = 125 °C JESD22a103
PC (JL3): Preconditioning (solder simulation)	The device is submitted to a typical temperature profile used for surface mounting, after controlled moisture absorption	
TC: Temperature Cycling	The device is submitted to cycled temperature excursions, between a hot and a cold chamber in air atmosphere	Ta Cycling: -40 °C ±125 °C JESD22a104
ESD (HBM): Electrostatic Discharge (Human Body Model)		Voltage ±2000 V JEDEC / JESD22-A114E
ESD (MM): Electrostatic Discharge (Machine Model)	The device is submitted to a high voltage peak on all his pins simulating ESD stress according to different simulation models.	Voltage ±200 V JEDEC/JESD-A115-A
ESD (CDM): Electrostatic Discharge (Charged Device Model)		Voltage ±750 V ANSI / ESD STM 5.3.1 ESDA
LU (CI): Latch-up (Overvoltage and Current Injection)	The device is submitted to a direct current forced/sunk into the input/output pins. Removing the direct current, no change in the supply current must be observed.	Current injection ±200 mA Overvoltage 1.5 x Vmax EIA/JESD78
THB: Temperature Humidity Bias	The device is biased in static configuration minimizing its internal power dissipation, and stored at controlled conditions for ambient temperature and relative humidity.	Vdd(nom) = 2.7 V T = 85 °C / RH = 85% JESD22a108
LTS: Low Temperature Storage	The device is stored in an unbiased condition at the min. temperature allowed by the package materials, sometimes lower than the min. op. temp	Ta = -40 °C JESD22a119
MS: Mechanical Shock	The device is submitted to 10000 g / 0.1 ms 5 shocks for each axis.	10000 g / 0.1 ms 5 shocks for each axis, under bias MIL STD 883MIL

Table 7: Tests and summary of results



7 Revision history

Table 8: Document revision history

Date	Revision	Changes
17-Nov-2016	1	Initial release
31-Aug-2017	2	Updated Figure 3: "MP23AB01DH electrical connections and external component values"



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